

Supporting information

**Enhancement of thermal energy transport across the
graphene/h-BN heterostructure interface**

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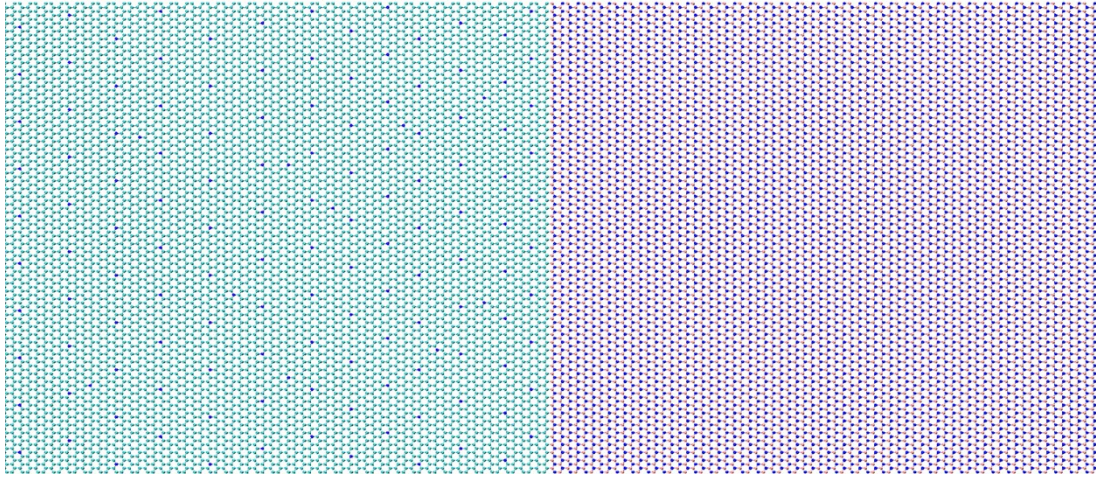


Figure S1. Distribution of N doping. The B, C, and N atoms are represented in pink, cyan, and blue color, respectively.

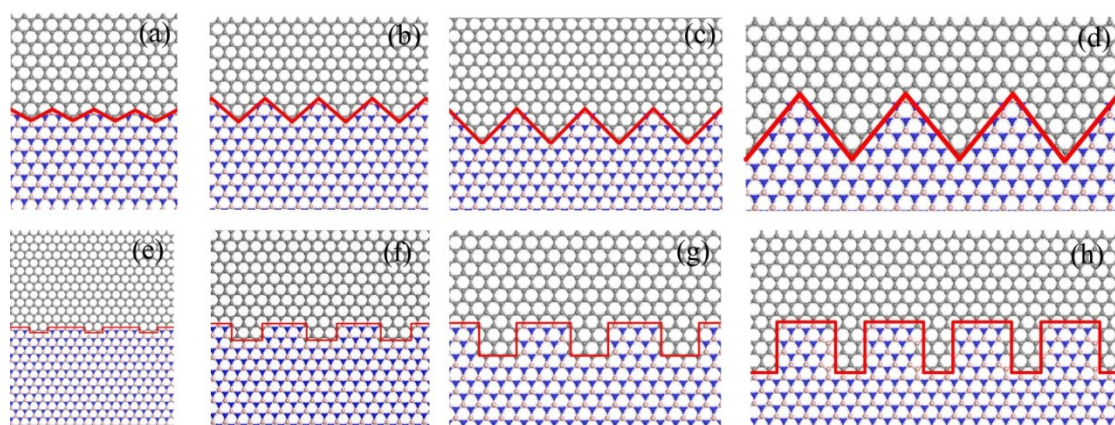


Figure S2. Different atomic row thicknesses for the zigzag and armchair interface topography: (a) and (e) single-row, (b) and (f) two-row, (c) and (g) three-row, (d) and (h) four-row.